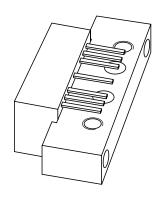
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



**BGD904; BGD904MI** 860 MHz, 20 dB gain power doubler amplifier

Product specification Supersedes data of 2000 Jan 10 2001 Nov 01



## 860 MHz, 20 dB gain power doubler amplifier

BGD904; BGD904MI

#### **FEATURES**

- · Excellent linearity
- · Extremely low noise
- · Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- · Gold metallization ensures excellent reliability.

### **APPLICATIONS**

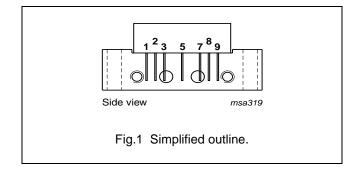
 CATV systems operating in the 40 to 900 MHz frequency range.

### **DESCRIPTION**

Hybrid amplifier modules in a SOT115J package operating with a voltage supply of 24 V (DC). Both modules are electrically identical, only the pinning is different.

### **PINNING - SOT115J**

PIN	DESCRIPTION		
PIN	BGD904	BGD904MI	
1	input	output	
2, 3	common	common	
5	+V <sub>B</sub>	+V <sub>B</sub>	
7, 8	common	common	
9	output	input	



### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Gp	power gain	f = 50 MHz	19.7	20.3	dB
		f = 900 MHz	20.5	21.5	dB
I <sub>tot</sub>	total current consumption (DC)	V <sub>B</sub> = 24 V	405	435	mA

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
V <sub>B</sub>	supply voltage		30	٧
Vi	RF input voltage		70	dBmV
T <sub>stg</sub>	storage temperature		+100	°C
T <sub>mb</sub>	operating mounting base temperature	-20	+100	°C

# 860 MHz, 20 dB gain power doubler amplifier

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### **CHARACTERISTICS**

Bandwidth 40 to 900 MHz;  $V_B$  = 24 V;  $T_{mb}$  = 35 °C;  $Z_S$  =  $Z_L$  = 75  $\Omega$ 

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 50 MHz	19.7	20	20.3	dB
		f = 900 MHz		21	21.5	dB
SL	slope straight line	f = 40 to 900 MHz	0.4	0.9	1.4	dB
FL	flatness straight line	f = 40 to 900 MHz	_	±0.15	±0.3	dB
S <sub>11</sub>	input return losses	f = 40 to 80 MHz	21	25	_	dB
		f = 80 to 160 MHz	22	30	_	dB
		f = 160 to 320 MHz	21	29	_	dB
		f = 320 to 550 MHz	18	24	_	dB
		f = 550 to 650 MHz	17	22	_	dB
		f = 650 to 750 MHz	16	21	_	dB
		f = 750 to 900 MHz	16	21	_	dB
S <sub>22</sub>	output return losses	f = 40 to 80 MHz	25	29	_	dB
		f = 80 to 160 MHz	23	28	_	dB
		f = 160 to 320 MHz	20	25	_	dB
		f = 320 to 550 MHz	20	24	_	dB
		f = 550 to 650 MHz	19	24	_	dB
		f = 650 to 750 MHz	18	24	_	dB
		f = 750 to 900 MHz	17	23	_	dB
S <sub>21</sub>	phase response	f = 50 MHz	-45	_	+45	deg
СТВ	composite triple beat	49 chs flat; V <sub>o</sub> = 47 dBmV; f <sub>m</sub> = 859.25 MHz	_	-68	-66.5	dB
		77 chs flat; $V_0 = 44 \text{ dBmV}$ ; $f_m = 547.25 \text{ MHz}$	_	-69.5	-67.5	dB
		110 chs flat; $V_0 = 44 \text{ dBmV}$ ; $f_m = 745.25 \text{ MHz}$	_	-63	-61.5	dB
		129 chs flat; $V_0 = 44 \text{ dBmV}$ ; $f_m = 859.25 \text{ MHz}$	_	-59.5	-57.5	dB
		110 chs; $f_m = 400 \text{ MHz}$ ; $V_0 = 49 \text{ dBmV at } 550 \text{ MHz}$ ; note 1	-	-63.5	-61.5	dB
		129 chs; f <sub>m</sub> = 650 MHz; V <sub>o</sub> = 49.5 dBmV at 860 MHz; note 2	_	-58.5	-56	dB
X <sub>mod</sub>	cross modulation	49 chs flat; V <sub>o</sub> = 47 dBmV; f <sub>m</sub> = 55.25 MHz	_	-66	-63	dB
illod		77 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 55.25 MHz	_	-68.5	-66	dB
		110 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 55.25 MHz	_	-65.5	-62.5	dB
		129 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 55.25 MHz	_	-64	-61	dB
		110 chs; f <sub>m</sub> = 400 MHz; V <sub>o</sub> = 49 dBmV at 550 MHz; note 1	_	-61.5	-59	dB
		129 chs; f <sub>m</sub> = 860 MHz; V <sub>o</sub> = 49.5 dBmV at 860 MHz; note 2	-	-60	-57	dB

BGD904; BGD904MI

## 860 MHz, 20 dB gain power doubler amplifier

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
CSO	composite second	49 chs flat; $V_0 = 47 \text{ dBmV}$ ; $_m = 860.5 \text{ MHz}$		-68	-62	dB
	order distortion	77 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 548.5 MHz		-72	-67	dB
		110 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 746.5 MHz	_	-68	-62	dB
		129 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 860.5 MHz	_	-64	-58	dB
		110 chs; f <sub>m</sub> = 250 MHz; V <sub>o</sub> = 49 dBmV at 550 MHz; note 1	-	-67	-62	dB
		129 chs; f <sub>m</sub> = 250 MHz; V <sub>o</sub> = 49.5 dBmV at 860 MHz; note 2	_	-62	-58	dB
d <sub>2</sub>	second order distortion	note 3	_	-82	-75	dB
		note 4	_	-82	-76	dB
		note 5	_	-83	-77	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$ ; note 6	64	65.5	_	dBmV
		$d_{im} = -60 \text{ dB}$ ; note 7	65	67	_	dBmV
		$d_{im} = -60 \text{ dB}$ ; note 8	67	69	_	dBmV
		CTB compression = 1 dB; 129 chs flat; f = 859.25 MHz	48.5	49	_	dBmV
		CSO compression = 1 dB; 129 chs flat; f = 860.5 MHz	50	52	_	dBmV
F	noise figure	f = 50 MHz	_	4	5	dB
		f = 550 MHz	_	4.5	5.5	dB
		f = 750 MHz	_	5.1	6.5	dB
		f = 900 MHz	_	6.2	7.5	dB
I <sub>tot</sub>	total current consumption (DC)	note 9		420	435	mA

### **Notes**

- 1. Tilt = 9 dB (50 to 550 MHz); tilt = 3.5 dB at -6 dB offset (550 to 750 MHz).
- 2. Tilt = 12.5 dB (50 to 860 MHz).
- 3.  $f_p = 55.25 \text{ MHz}$ ;  $V_p = 44 \text{ dBmV}$ ;  $f_q = 805.25 \text{ MHz}$ ;  $V_q = 44 \text{ dBmV}$ ; measured at  $f_p + f_q = 860.5 \text{ MHz}$ .
- 4.  $f_p = 55.25 \text{ MHz}$ ;  $V_p = 44 \text{ dBmV}$ ;  $f_q = 691.25 \text{ MHz}$ ;  $V_q = 44 \text{ dBmV}$ ; measured at  $f_p + f_q = 746.5 \text{ MHz}$ .
- 5.  $f_p = 55.25 \text{ MHz}$ ;  $V_p = 44 \text{ dBmV}$ ;  $f_q = 493.25 \text{ MHz}$ ;  $V_q = 44 \text{ dBmV}$ ; measured at  $f_p + f_q = 548.5 \text{ MHz}$ .
- 6. Measured according to DIN45004B:

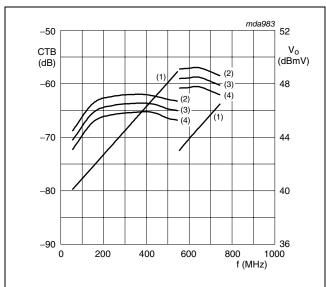
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f_p = 851.25 \text{ MHz}; V_p = V_0; f_q = 858.25 \text{ MHz}; V_q = V_0 - 6 \text{ dB};
```

 $f_r = 860.25 \text{ MHz}$ ;  $V_r = V_o - 6 \text{ dB}$ ; measured at  $f_p + f_q - f_r = 849.25 \text{ MHz}$ .

- 7. Measured according to DIN45004B:
  - $f_p=740.25~\text{MHz};~V_p=V_o;~f_q=747.25~\text{MHz};~V_q=V_o-6~\text{dB};~f_r=749.25~\text{MHz};~V_r=V_o-6~\text{dB};~\text{measured at}~f_p+f_q-f_r=738.25~\text{MHz}.$
- 8. Measured according to DIN45004B:
  - $f_p=540.25$  MHz;  $V_p=V_o;$   $f_q=547.25$  MHz;  $V_q=V_o$  –6 dB;  $f_r=549.25$  MHz;  $V_r=V_o$  –6 dB; measured at  $f_p+f_q-f_r=538.25$  MHz.
- 9. The module normally operates at  $V_B$  = 24 V, but is able to withstand supply transients up to 35 V.

## 860 MHz, 20 dB gain power doubler amplifier

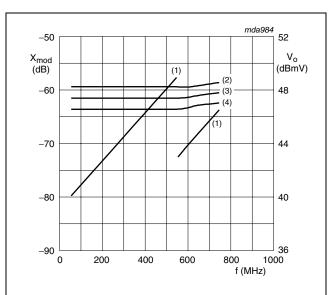
BGD904; BGD904MI



 $Z_S$  =  $Z_L$  = 75  $\Omega;$   $V_B$  = 24 V; 110 chs; tilt = 9 dB (50 to 550 MHz); tilt = 3.5 dB at –6 dB offset (550 to 750 MHz).

- (1) V<sub>c</sub>
- (3) Typ.
- (2) Typ. +3  $\sigma$ . (4) Typ. -3  $\sigma$ .

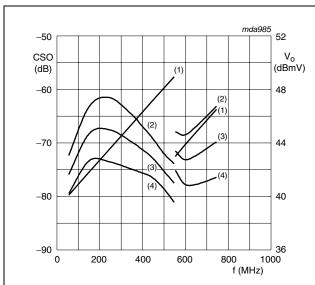
Fig.2 Composite triple beat as a function of frequency under tilted conditions.



 $Z_S$  =  $Z_L$  = 75  $\Omega;$   $V_B$  = 24 V; 110 chs; tilt = 9 dB (50 to 550 MHz); tilt = 3.5 dB at –6 dB offset (550 to 750 MHz).

- (1) V<sub>o</sub>.
- (3) Typ.
- (2) Typ. +3 σ.
- (4) Typ. –3 σ.

Fig.3 Cross modulation as a function of frequency under tilted conditions.



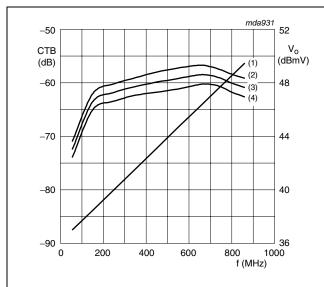
 $Z_S=Z_L=75~\Omega;~V_B=24~V;~110~chs;~tilt=9~dB~(50~to~550~MHz);~tilt=3.5~dB~at~-6~dB~offset~(550~to~750~MHz).$ 

- (1) V
- (3) Typ.
- (2) Typ. +3 σ.
- (4) Typ. –3 σ.

Fig.4 Composite second order distortion as a function of frequency under tilted conditions.

## 860 MHz, 20 dB gain power doubler amplifier

BGD904; BGD904MI



 $Z_{S}$  =  $Z_{L}$  = 75  $\Omega;$   $V_{B}$  = 24 V; 129 chs;

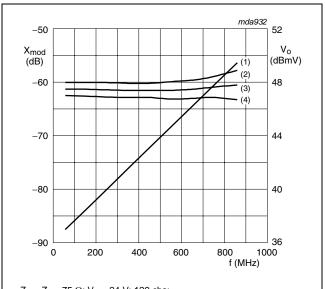
tilt = 12.5 dB; (50 to 860 MHz).

(1) V<sub>o</sub>.

(3) Typ.

(2) Typ. +3  $\sigma$ . (4) Typ. -3  $\sigma$ .

Fig.5 Composite triple beat as a function of frequency under tilted conditions.



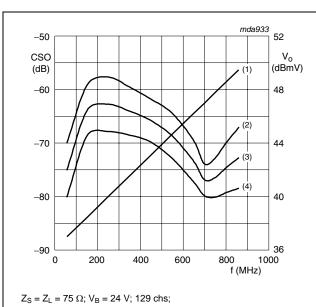
 $Z_S = Z_L = 75~\Omega; V_B = 24~V; 129~chs;$  tilt = 12.5 dB; (50 to 860 MHz).

(1) V<sub>o</sub>.

(3) Typ.

(2) Typ. +3  $\sigma$ . (4) Typ. -3  $\sigma$ .

Fig.6 Cross modulation as a function of frequency under tilted conditions.



 $Z_S = Z_L = 75 \Omega$ ;  $V_B = 24 V$ ; 129 chs; tilt = 12.5 dB; (50 to 860 MHz).

(1)  $V_0$ .

(3) Typ.

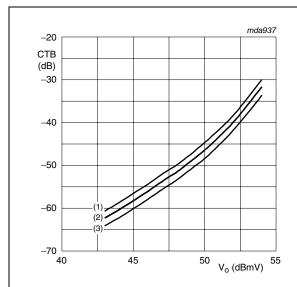
(2) Typ. +3  $\sigma$ .

(4) Typ. –3 σ.

Fig.7 Composite second order distortion as a function of frequency under tilted conditions.

## 860 MHz, 20 dB gain power doubler amplifier

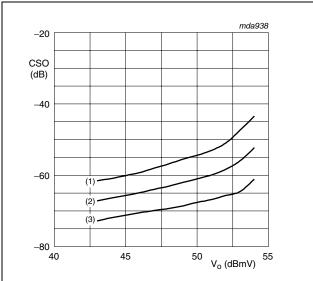
BGD904; BGD904MI



 $Z_S$  =  $Z_L$  = 75  $\Omega;\,V_B$  = 24 V; 129 chs;  $f_m$  = 859.25 MHz.

- (1) Typ.  $+3 \sigma$ .
- (2) Typ.
- (3) Typ.  $-3 \sigma$ .

Fig.8 Composite triple beat as a function of output voltage.



 $Z_S = Z_L = 75~\Omega; V_B = 24~V; 129~chs; f_m = 860.5~MHz.$ 

- (1) Typ. +3 σ.
- (2) Typ.

7

(3) Typ.  $-3 \sigma$ .

Fig.9 Composite second order distortion as a function of output voltage.

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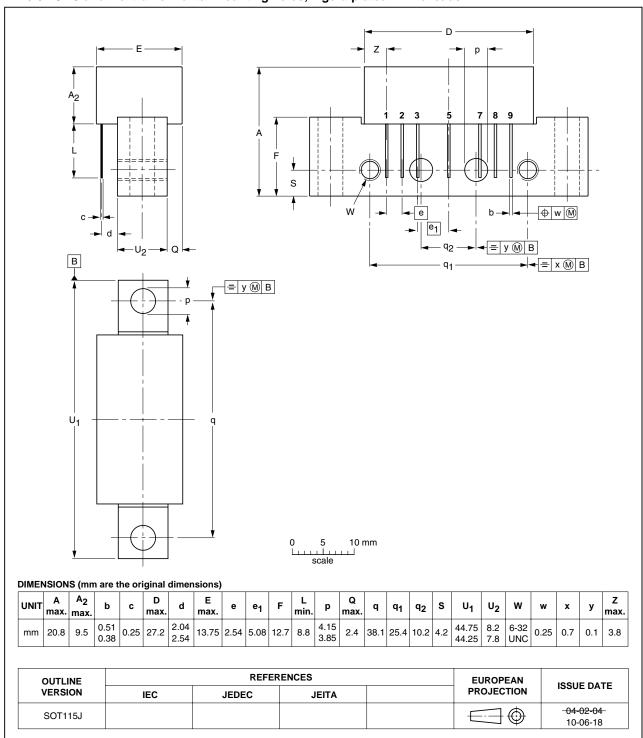
## 860 MHz, 20 dB gain power doubler amplifier

BGD904; BGD904MI

### **PACKAGE OUTLINE**

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



### 860 MHz, 20 dB gain power doubler amplifier

BGD904; BGD904MI

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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